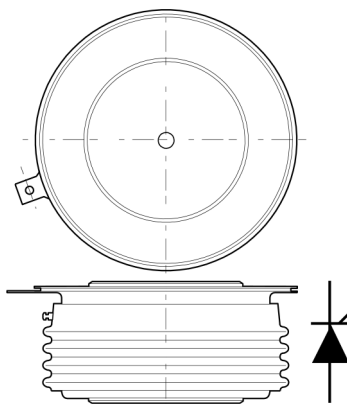


# Phase Control Thyristor

**multicomp**PRO

RoHS  
Compliant



Outline type code: G

## Features

- Double Side Cooling
- High Surge Capability

## Applications

- High Power Drives
- High Voltage Power Supplies
- Static Switches

## Key Parameters

Part Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	$I_{T(AV)}$	$I_{TSM}$	$dV/dt^*$	$dI/dt$	Conditions
MPPCT960G180	1800	960 A	14000 A	1000 V/ $\mu$ s	200 A/ $\mu$ s	$T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 60\text{mA}$ , $V_{DRM}$ , $V_{RRM}$ $t_p = 10\text{ms}$ , $V_{DSM}$ & $V_{RSM} =$ $V_{DRM}$ & $V_{RRM} + 100\text{V}$ respectively

\* Higher  $dV/dt$  selections available

## Current Ratings

$T_{case} = 60^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	960	A
$I_{T(RMS)}$	RMS value	-	1510	
$I_T$	Continuous (direct) on-state current	-	1360	

## Surge Ratings

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$ $V_R = 0$	14	kA
$I^2t$	$I^2t$ for fusing		0.98	$\text{MA}^2\text{s}$

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## Thermal and Mechanical Ratings

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.35	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink				0.008	
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / V <sub>RRM</sub>				125
T <sub>stg</sub>	Storage temperature range			-40	140	
F <sub>m</sub>	Clamping force			12	18	kN

## Dynamic Characteristics

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$I_{RRM}/I_{DRM}$	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$		-	60	mA
$dV/dt$	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125^{\circ}C$ , gate open		1000	-	V/ $\mu s$
$dI/dt$	Rate of rise of on-state current	From 67% $V_{DRM}$ to 1000A Gate source 30V, 10 $\Omega$ , $t_r < 0.5\mu s$ , $T_j = 125^{\circ}C$	Repetitive 50Hz	-	200	A/ $\mu s$
			Non-repetitive		1000	
$V_T$	On-state voltage	$I_T = 1500A$ , $T_{case} = 125^{\circ}C$			1.45	V
$V_{T(TO)}$	Threshold voltage	$T_{case} = 125^{\circ}C$			0.91	
$r_T$	On-state slope resistance	$T_{case} = 125^{\circ}C$			0.36	m $\Omega$
$t_{gd}$	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$ $t_r = 0.5\mu s$ , $T_j = 25^{\circ}C$			3	$\mu s$
$t_q$	Turn-off time	$T_j = 125^{\circ}C$ , $V_R = 100V$ , $dI/dt = 10A/\mu s$ , $dV_{DR}/dt = 20V/\mu s$ linear to 67% $V_{DRM}$			200	
$Q_S$	Stored charge	$I_T = 1000A$ , $t_p = 1000\mu s$ , $T_j = 125^{\circ}C$ , $dI/dt = 10A/\mu s$ ,			2000	$\mu C$
$I_{RR}$	Reverse recovery current				120	A
$I_L$	Latching current	$T_j = 25^{\circ}C$ ,			1	
$I_H$	Holding current	$T_j = 25^{\circ}C$ ,			200	mA

## Gate Trigger Characteristics and Ratings

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$	3	V
$V_{GD}$	Gate non-trigger voltage	At 40% $V_{DRM}$ , $T_{case} = 125^{\circ}C$	0.3	
$I_{GT}$	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$	300	mA
$I_{GD}$	Gate non-trigger current	At 40% $V_{DRM}$ , $T_{case} = 125^{\circ}C$	20	

## Performance Curves

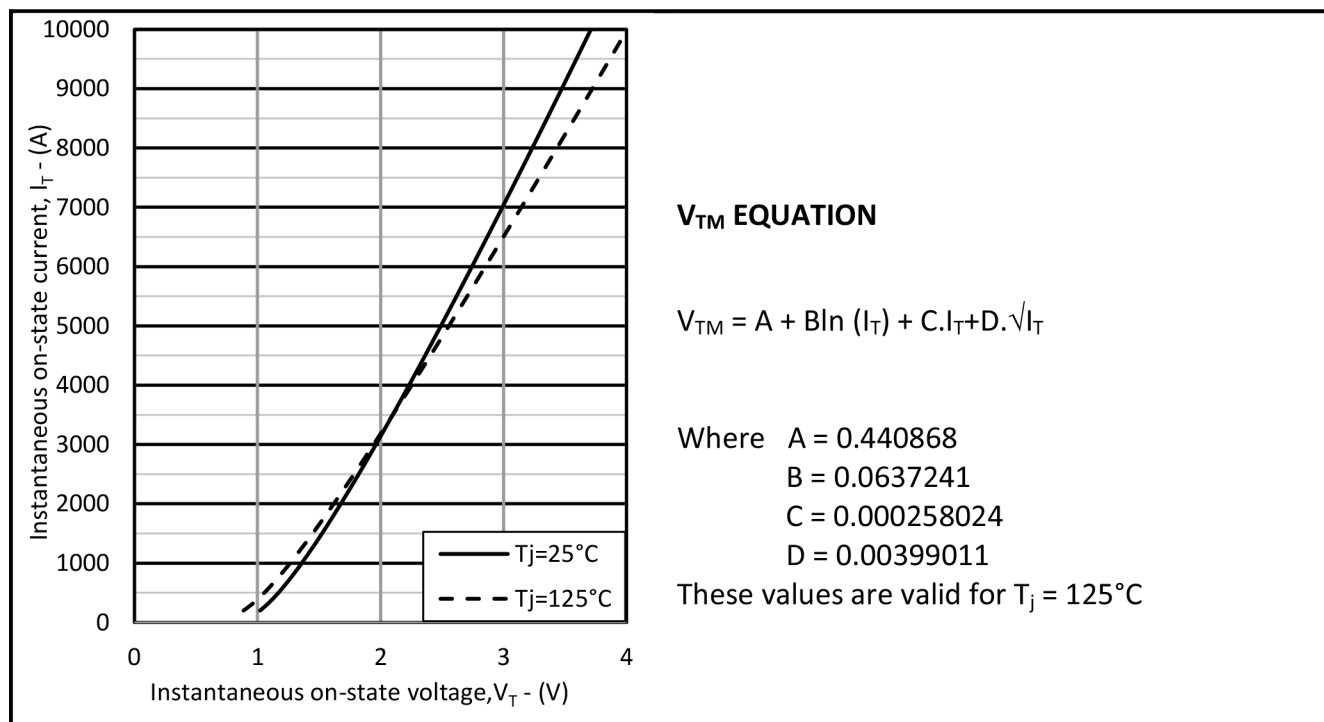


Fig.2 Maximum & minimum on-state characteristics

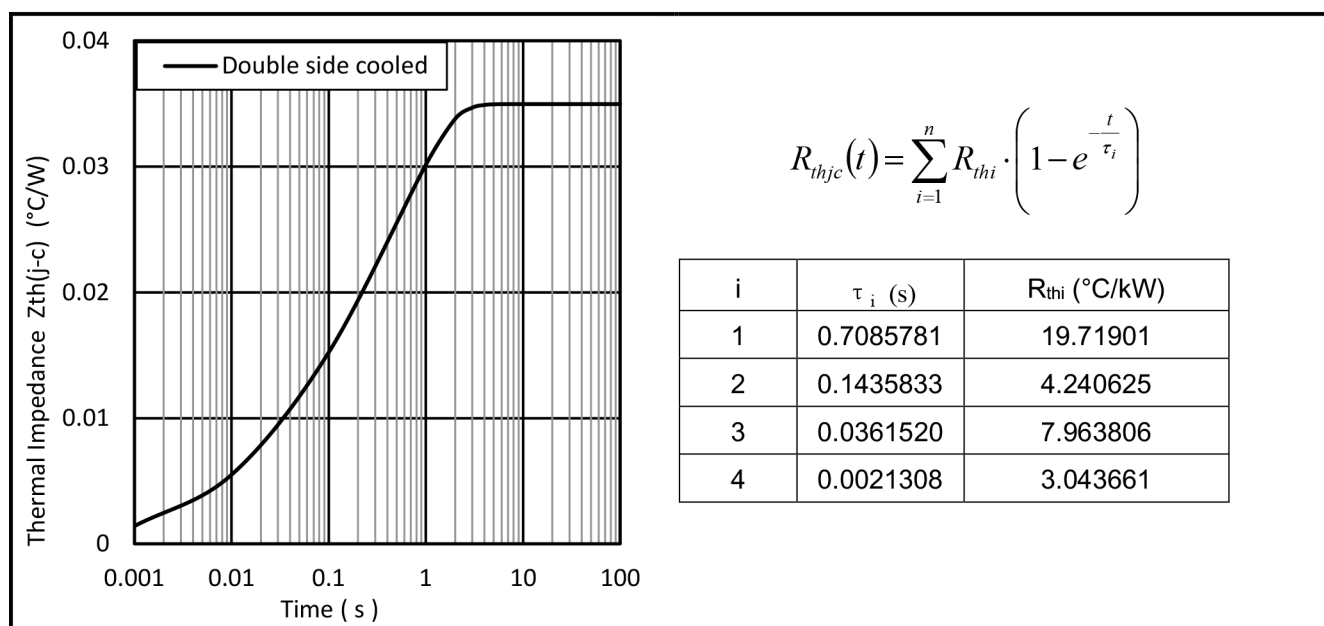
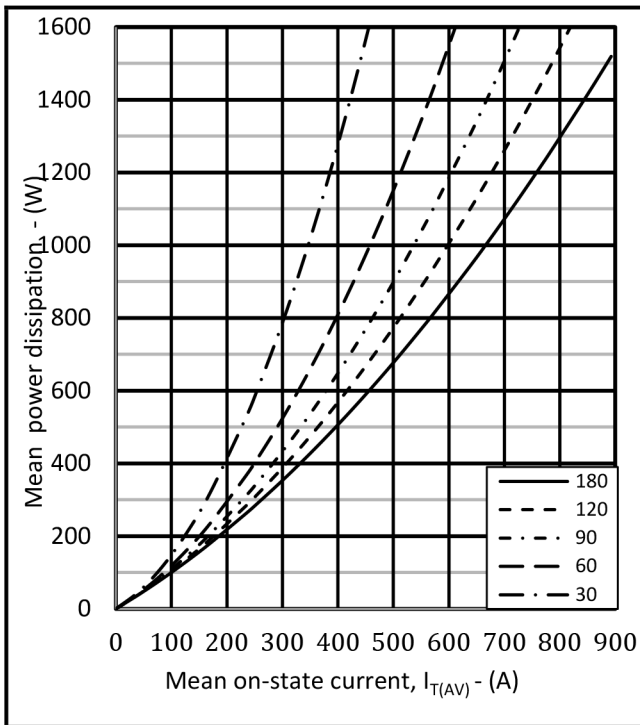
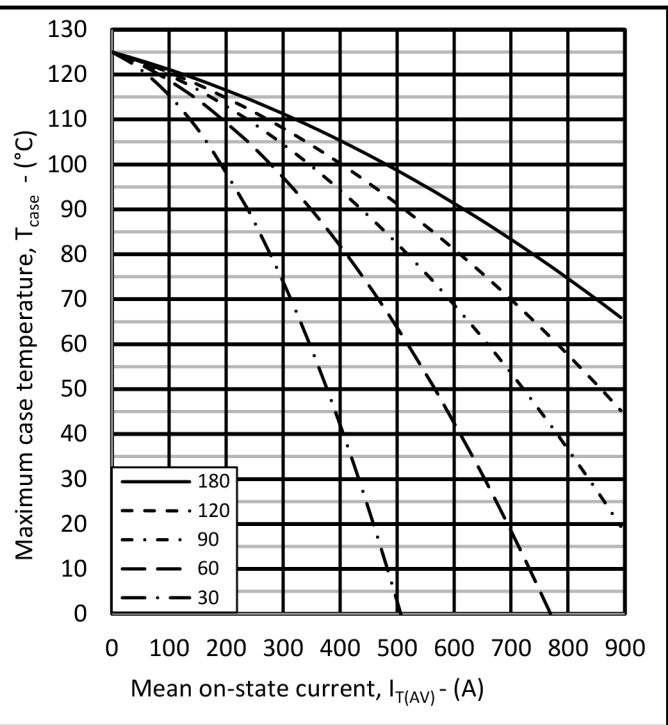


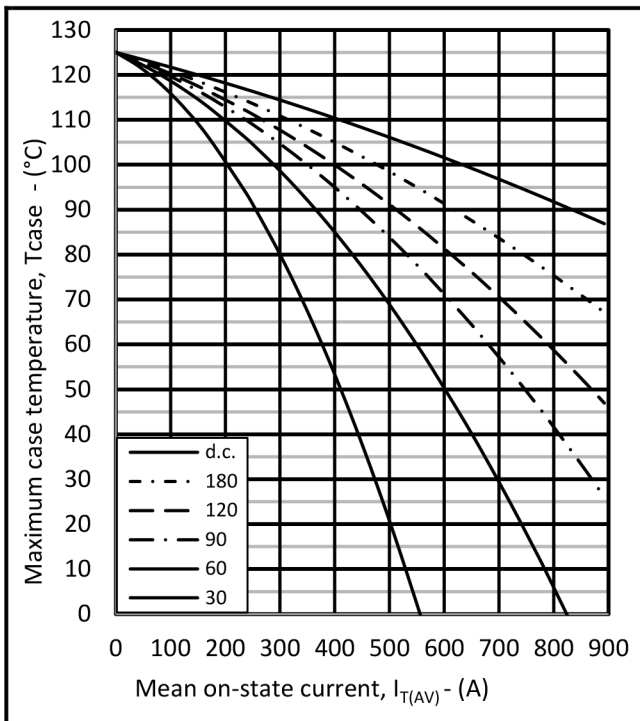
Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)



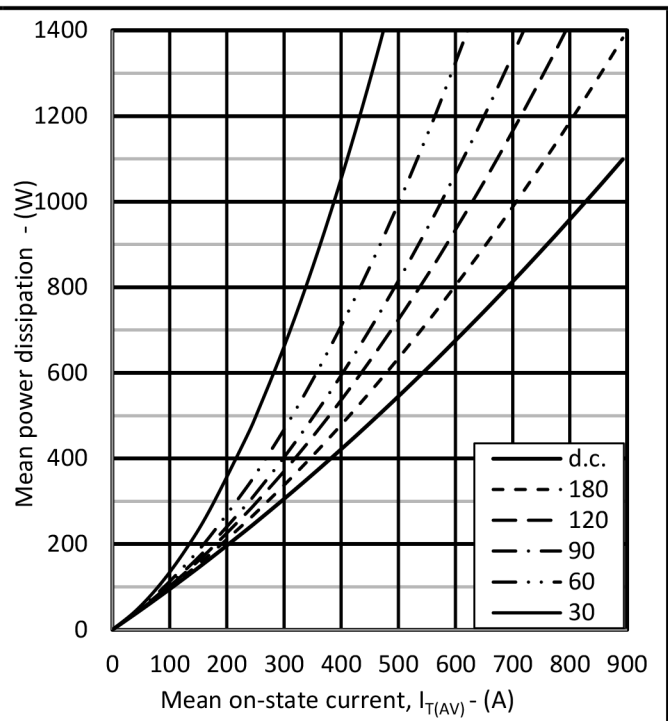
**Fig.4 On-state power dissipation – sine wave**



**Fig.5 Maximum permissible case temperature, double side cooled – sine wave**



**Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave**



**Fig.7 On-state power dissipation – rectangular wave**

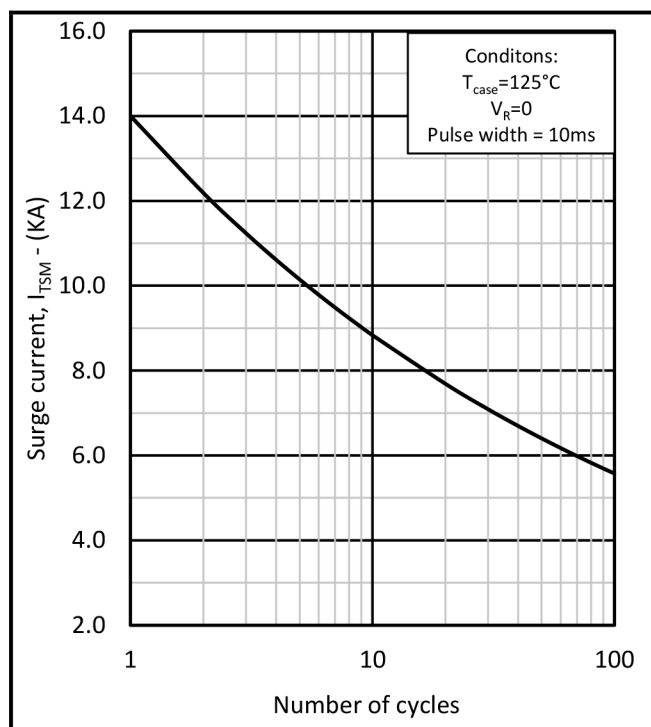


Fig.8 Multi-cycle surge current

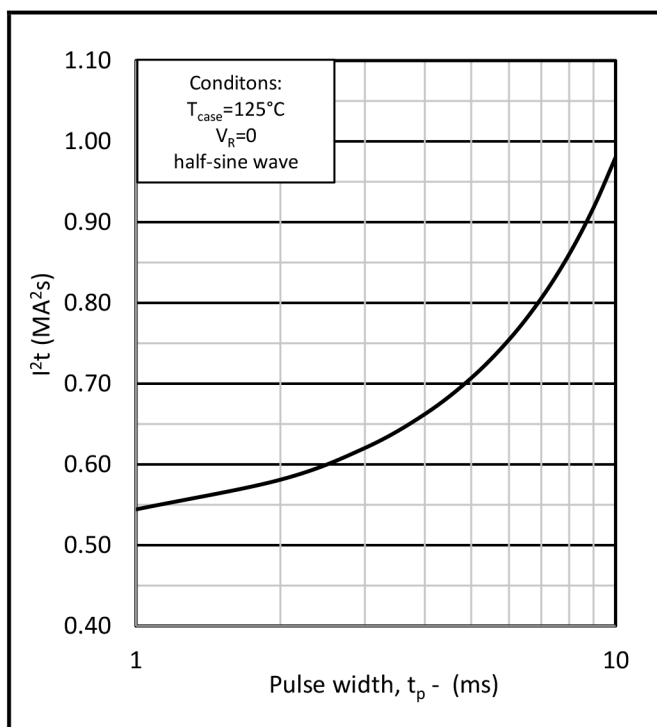


Fig.9 Single-cycle  $I^2t$

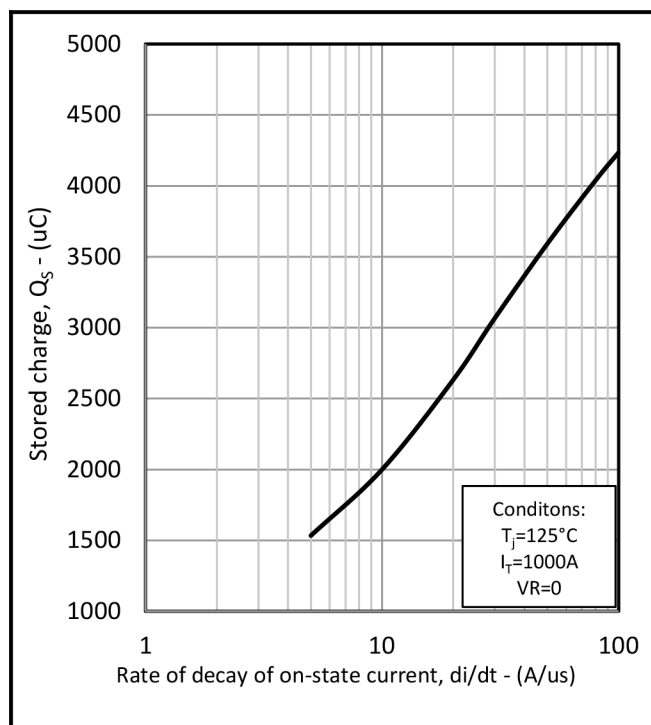


Fig.10 Stored charge vs  $di/dt$

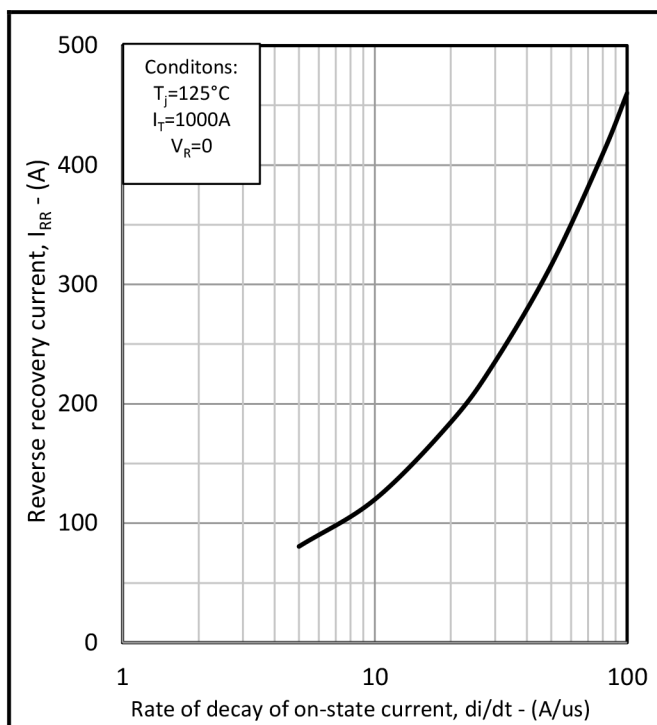


Fig.11 Reverse recovery current vs  $di/dt$

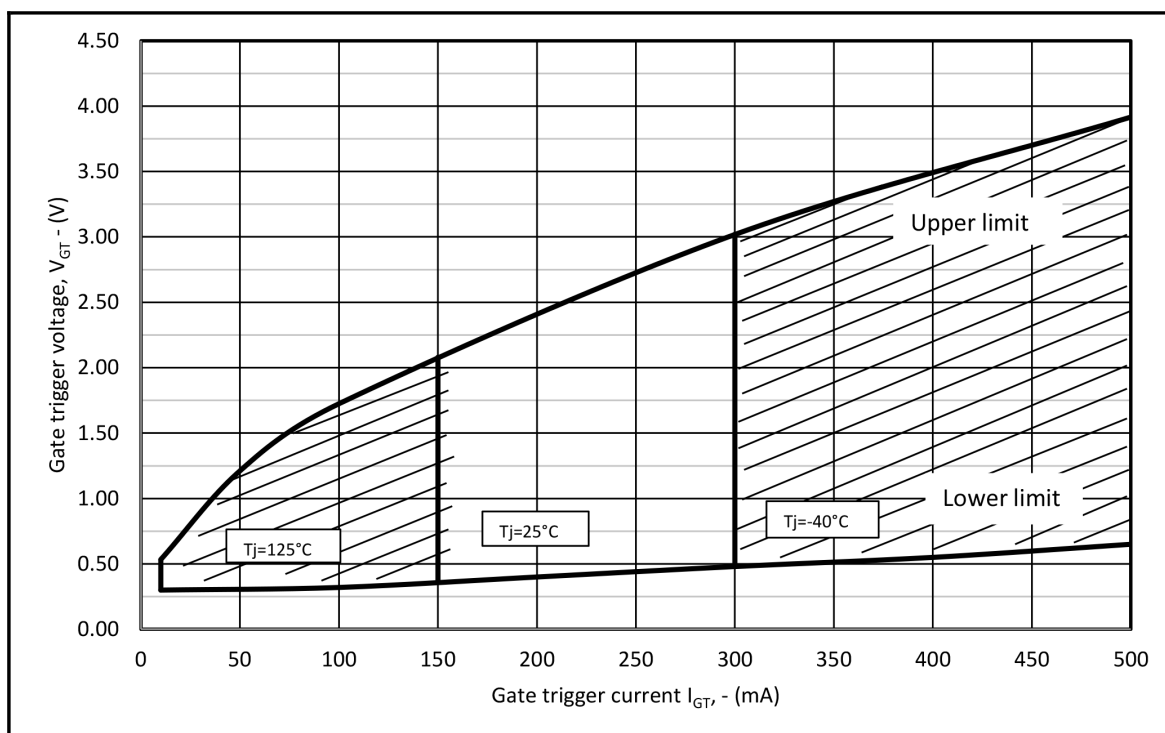


Fig.12 Gate characteristics

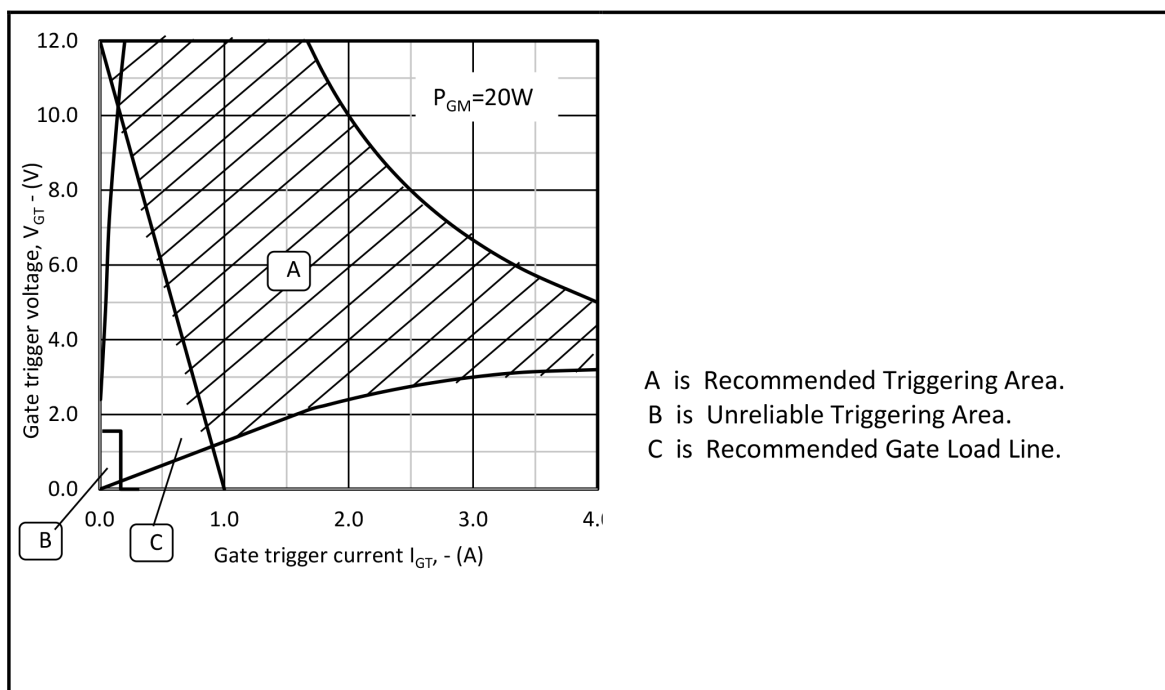
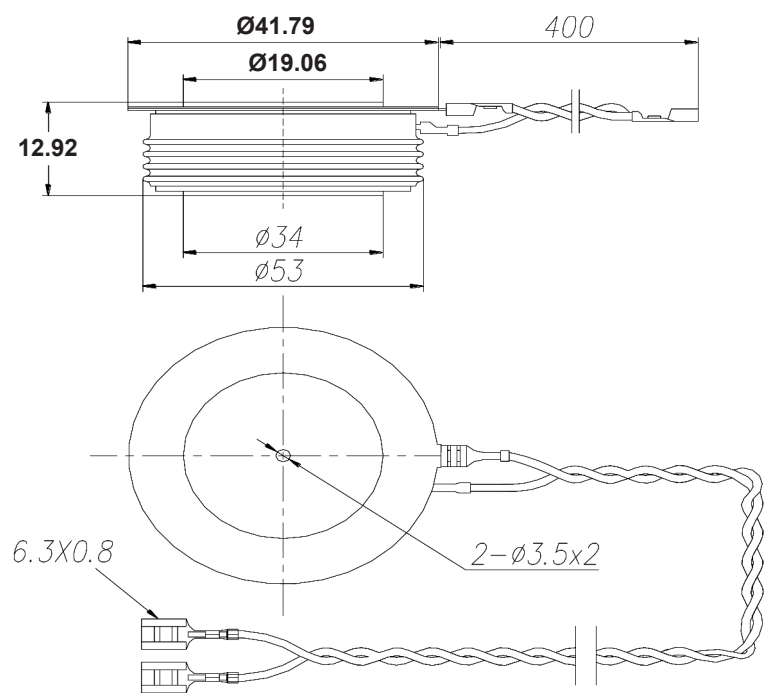


Fig.13 Gate characteristics

Phase Control Thyristor

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Package outline type code: G

Part Number Table

Description	Part Number
Phase Control Thyristor Module, 1800V, 960A, G Case Code	MPPCT960G180

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